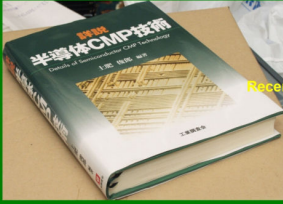


Doi Laboratory's Activities



"Linear Contact Drum Type CMP System" proposed by Prof. Doi

Photos of the experiments (Clean room in Doi Lab.)



E-mail: doi@post.saitama-u.ac.jp

Recent publication
"Details of Semiconductor CMP Technology"
(Kogyo Chosakai Publishing Co.,Ltd.)

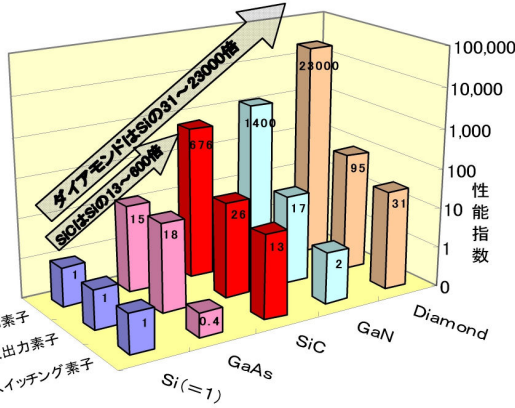
ポスト・シリコンデバイスをねらう単結晶SiCのCMP

- 1) 加工環境を制御したベルジャー式CMP装置の考案
- 2) 各種加工物のベルジャー式CMP特性と加工メカニズム
- 3) 単結晶SiC基板への適用
 - ① 高圧酸素雰囲気におけるベルジャー式CMP
 - ② 高圧酸素雰囲気下で光触媒反応を援用したベルジャー型CMP

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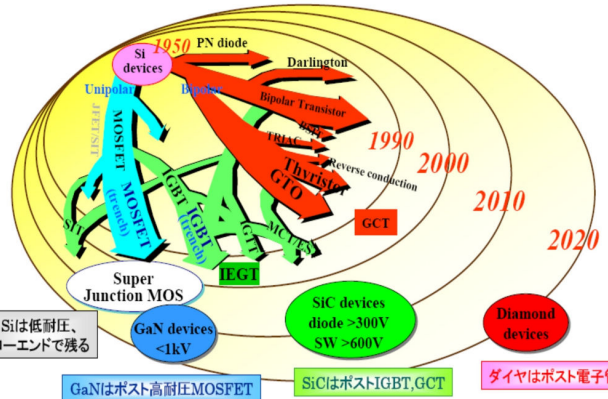
e-mail: doi@post.saitama-u.ac.jp



ワイドギャップ半導体デバイスの性能指数の比較 (Siデバイスを1としたとき)

(産総研資料より)

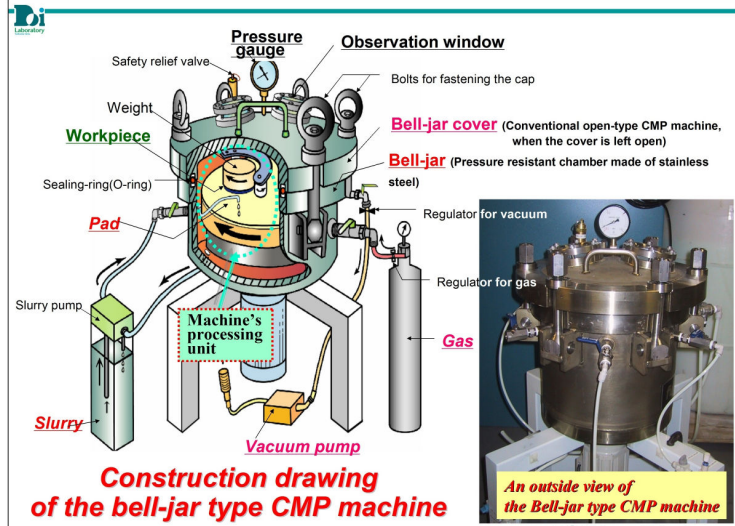
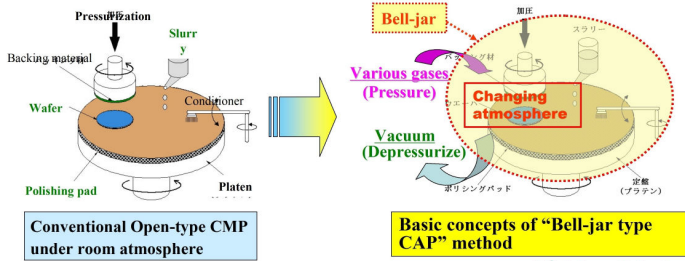
パワーデバイス開発の歴史 (東芝・四戸)



Siは低耐圧、ローエンドで残る
GaNはポスト高耐圧MOSFET
SiCはポストIGBT,GCT
ダイヤモンドはポスト電子管?

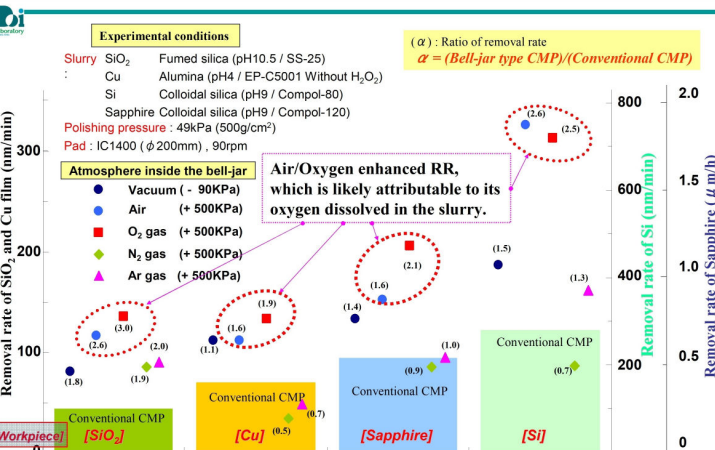
Proposal "A New Bell-Jar Type Controlled Atmosphere Polishing Method & Machine"

- ★ New CMP machine entirely covered with a bell-jar (Chamber) to control processing atmosphere
e.g. temperature, humidity, atmosphere, gas and oxygen dissolved in slurry
- ★ Study on CMP processing mechanism

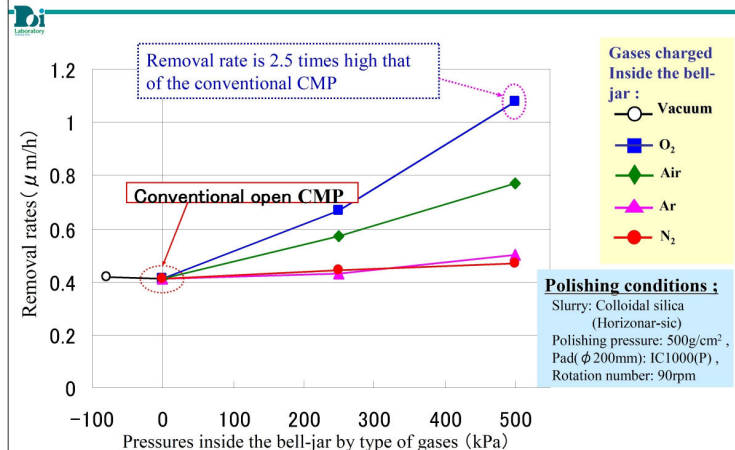


Construction drawing of the bell-jar type CMP machine

An outside view of the bell-jar type CMP machine



Removal rates of SiO₂, Cu, sapphire and silicon when inside the bell-jar is pressurized at 500kPa with various gases & comparison with the removal rate of the conventional CMP



Relation between the removal rates of SiC single crystal and the pressures inside the bell-jar

Chemically & Mechanically very stable